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List of Publications

1. **Pal, N.**, Sharma, A., Acharya, V., Chourasia, N. K., Biring, S., & Pal, B. N. (2019). Gate interface engineering for subvolt metal oxide transistor fabrication by using ion-conducting dielectric with Mn₂O₃ gate interface. *ACS Applied Electronic Materials*, **2(1)**, 25-34.
2. **Pal, N.**, Pandey, U., Biring, S., & Pal, B. N. (2022). Solution processed low-voltage metal-oxide transistor by using TiO₂/Li–Al₂O₃ stacked gate dielectric. *Journal of Materials Science: Materials in Electronics*, **1-10**.
3. Sharma, A., Chourasia, N. K., **Pal, N.**, Biring, S., & Pal, B. N. (2019). Role of electron donation of TiO₂ gate interface for developing solution-processed high-performance one-volt metal-oxide thin-film transistor using ion-conducting gate dielectric. *The Journal of Physical Chemistry C*, **123(33)**, 20278-20286.
4. Sharma, A., Chourasia, N. K., Acharya, V., **Pal, N.**, Biring, S., Liu, S. W., & Pal, B. N. (2020). Ultra-low voltage metal oxide thin film transistor by low-temperature annealed solution processed LiAlO₂ gate dielectric. *Electronic Materials Letters*, **16(1)**, 22-34.
5. Chourasia, N. K., Sharma, A., Acharya, V., **Pal, N.**, Biring, S., & Pal, B. N. (2019). Solution processed low band gap ion-conducting gate dielectric for low voltage metal oxide transistor. *Journal of Alloys and Compounds*, **777**, 1124-1132.
6. Chourasia, N. K., Sharma, A., **Pal, N.**, Biring, S., & Pal, B. N. (2020). Dielectric/Semiconductor Interfacial p-Doping: A New Technique to Fabricate

Solution-Processed High-Performance 1 V Ambipolar Oxide Transistors. *Physica status solidi (RRL)–Rapid Research Letters*, **14(10)**, 2000268.

7. Pandey, U., Chourasia, N. K., **Pal, N.**, Biring, S., & Pal, B. N. (2022). Functional Dielectric Properties of Solution-Processed Lithium Indium Tin Oxide (LiInSnO₄) and Its Application as a Gate Insulator of a Low Voltage Thin Film Transistor. *IEEE Transactions on Electron Devices*, **69(3)**, 1077-1082.
8. Acharya, V., **Pal, N.**, Sharma, A., Pandey, U., Biring, S., & Pal, B. N. Solution processed low operating voltage SnO₂ thin film transistor by using LiSnO₃ gate dielectric. **Materials Science & Engineering B. (Under Revision)**